
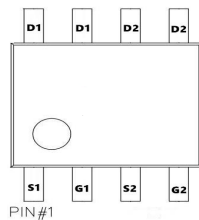
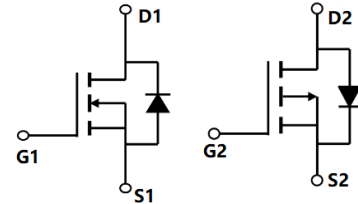
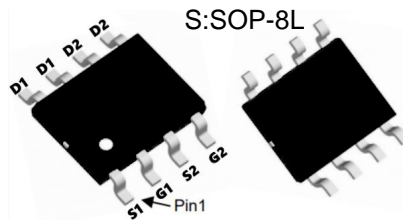


**TM10G04S/TM4614A****N+P-Channel Enhancement Mode Mosfet**

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>Product Summary</p> <p>N Channel</p> <p>$V_{DS} = 40V, I_D = 9.8A$ $R_{DS(ON)} = 16m\Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>P Channel</p> <p>$V_{DS} = -40V, I_D = -7.5A$ $R_{DS(ON)} = 36m\Omega$ (typ.) @ $V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Marking: 10G04 OR 4614A

**Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9.8	-7.5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.5	-5.8	A
I_{DM}	Pulsed Drain Current ²	23	-22	A
EAS	Single Pulse Avalanche Energy ³	16.2	39	mJ
I_{AS}	Avalanche Current	18	-28	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	1.67	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	75		$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	30		$^\circ C/W$

TM10G04S/TM4614A

N+P-Channel Enhancement Mode Mosfet

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25 °C, I _D =1mA	---	0.034	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	---	16	19	mΩ
		V _{GS} =4.5V, I _D =4A	---	19	25	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.75	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-4.56	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =5A	---	14	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.6	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V, V _{GS} =4.5V, I _D =5A	---	5.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.25	---	
Q _{gd}	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	V _{DD} =20V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	8.9	---	ns
T _r	Rise Time		---	2.2	---	
Td(off)	Turn-Off Delay Time		---	41	---	
T _f	Fall Time		---	2.7	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	593	---	pF
C _{oss}	Output Capacitance		---	76	---	
Cr _{ss}	Reverse Transfer Capacitance		---	56	---	
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	6.1	A
ISM	Pulsed Source Current ^{2,5}		---	---	23	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _s =1A, T _J =25°C	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed, pulse width ≦ 300us, duty cycle ≦ 2%
- 3、The EAS data shows Max. rating. The test condition is VDD=25V, VGS=10V, L=0.1mH, IAS=17.8A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation



TM10G04S/TM4614A

N+P-Channel Enhancement Mode Mosfet

P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-40	---	---	V
$\Delta BVDSS/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.02	---	V/ $^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-6A$	---	36	39	m Ω
		$V_{GS}=-4.5V, I_D=-3A$	---	42	49	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.72	---	mV/ $^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V, I_D=-6A$	---	13	---	S
Qg	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-4.5V, I_D=-6A$	---	11.5	---	nC
Qgs	Gate-Source Charge		---	3.5	---	
Qgd	Gate-Drain Charge		---	3.3	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	22	---	ns
T _r	Rise Time		---	15.7	---	
Td(off)	Turn-Off Delay Time		---	59	---	
T _f	Fall Time		---	5.5	---	
C _{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	1415	---	pF
C _{oss}	Output Capacitance		---	134	---	
C _{rss}	Reverse Transfer Capacitance		---	102	---	
I _s	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{Force Current}$	---	---	-6	A
ISM	Pulsed Source Current ^{2,5}		---	---	-22	A
VSD	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-27.2A$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.



TM10G04S/TM4614A

N+P-Channel Enhancement Mode Mosfet

N-Channel Typical Characteristics

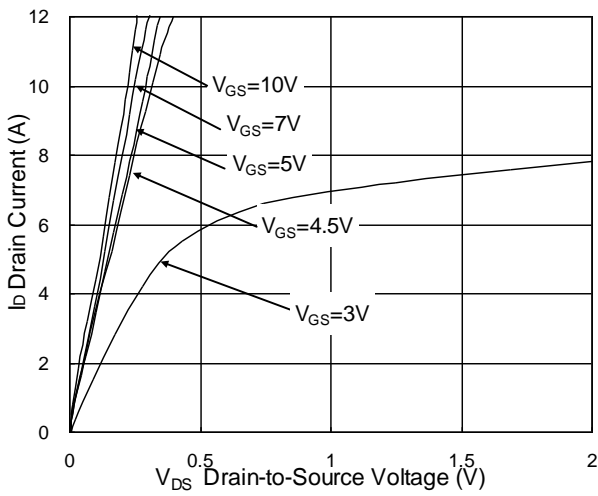


Fig.1 Typical Output Characteristics

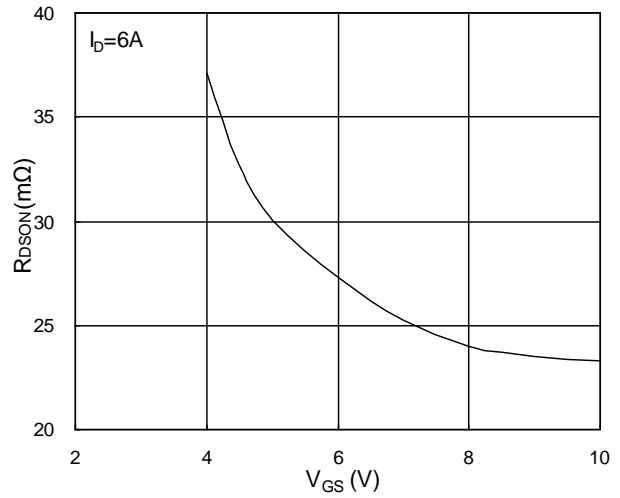


Fig.2 On-Resistance vs. G-S Voltage

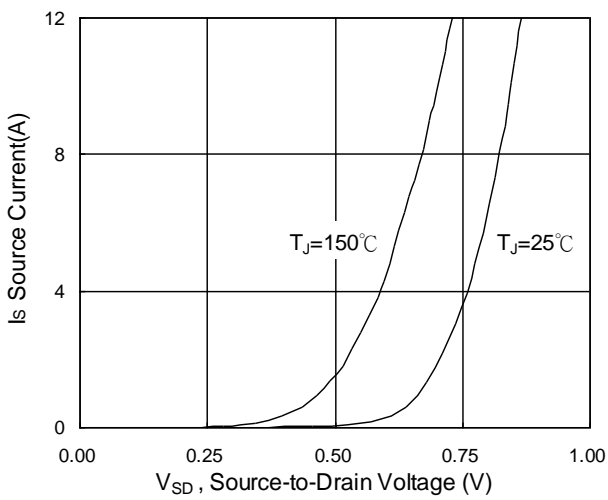


Fig.3 Source Drain Forward Characteristics

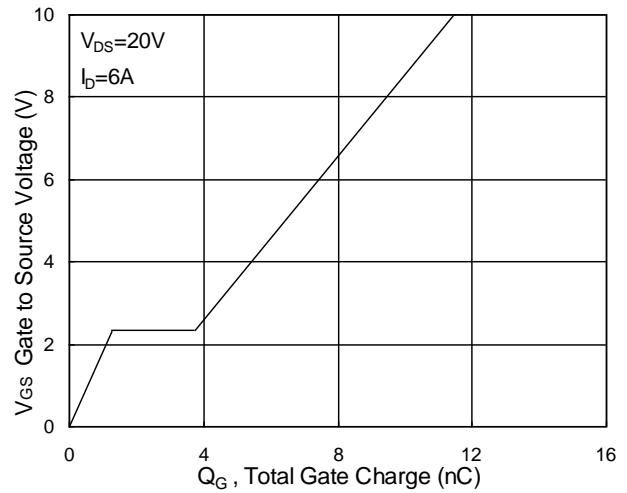


Fig.4 Gate-Charge Characteristics

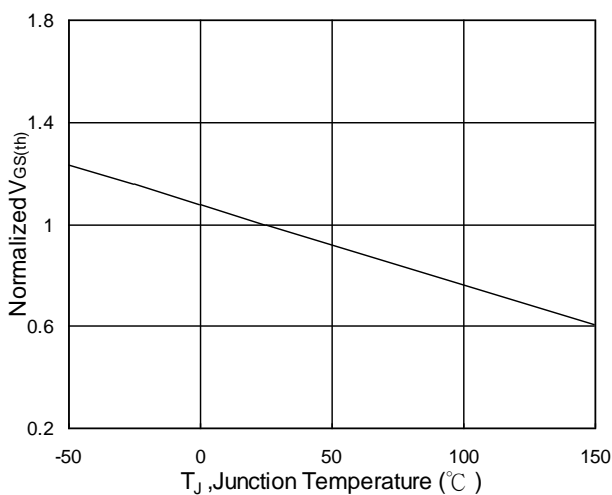


Fig.5 Normalized V_{GS(th)} vs. T_J

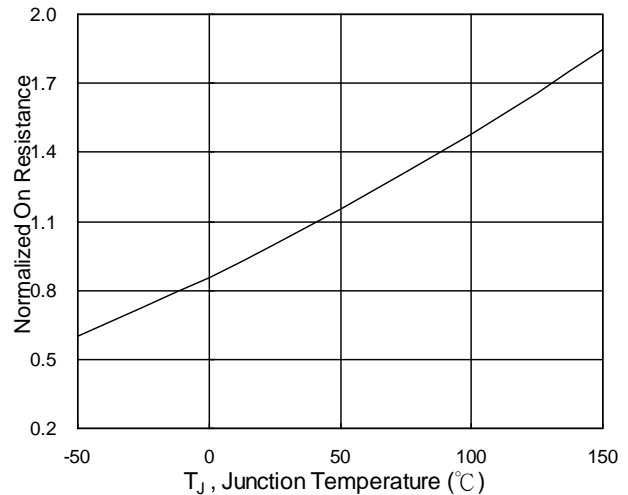


Fig.6 Normalized R_{DS(on)} vs. T_J

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N+P-Channel Enhancement Mode Mosfet

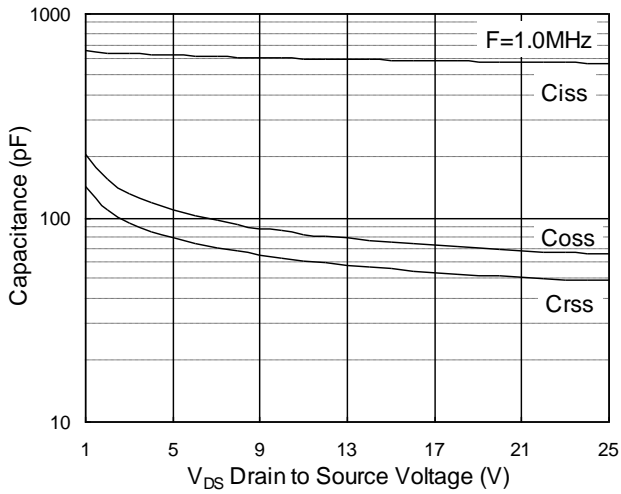


Fig.7 Capacitance

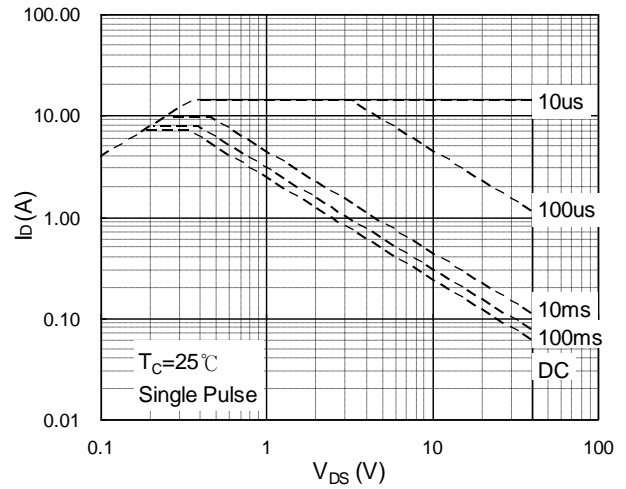


Fig.8 Safe Operating Area

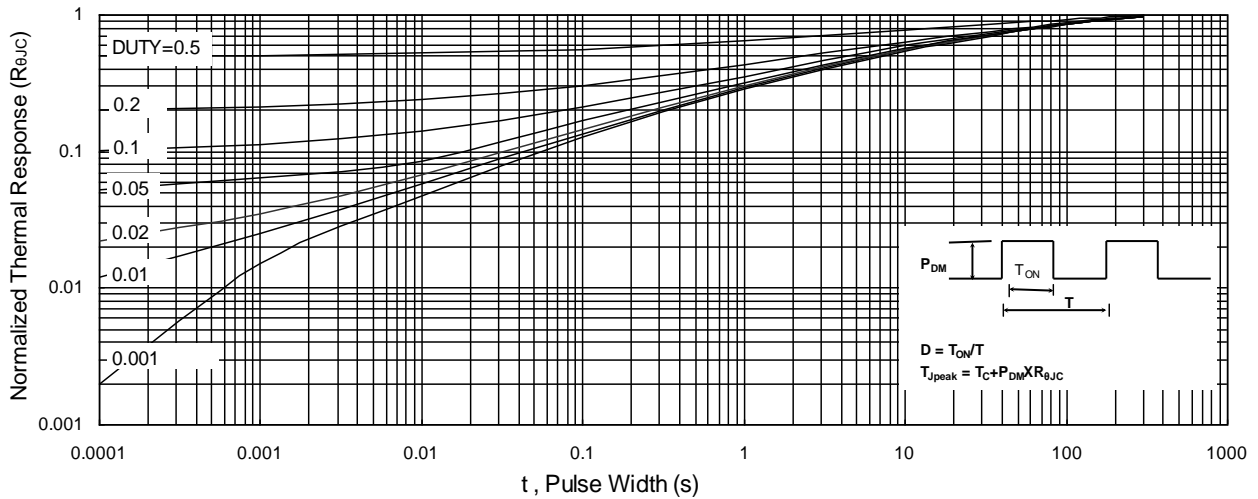


Fig.9 Normalized Maximum Transient Thermal Impedance

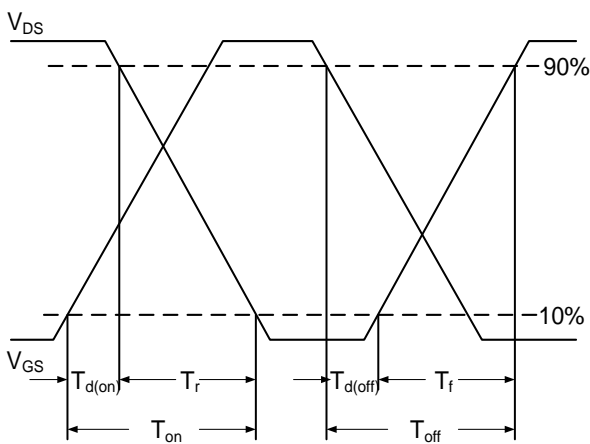


Fig.10 Switching Time Waveform

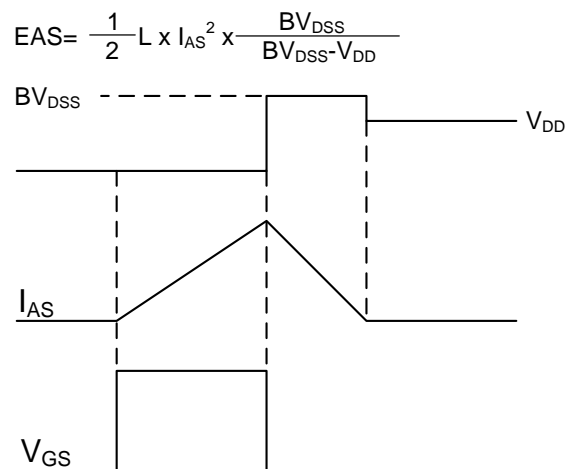


Fig.11 Unclamped Inductive Waveform



TM10G04S/TM4614A

N+P-Channel Enhancement Mode Mosfet

P-Channel Typical Characteristics

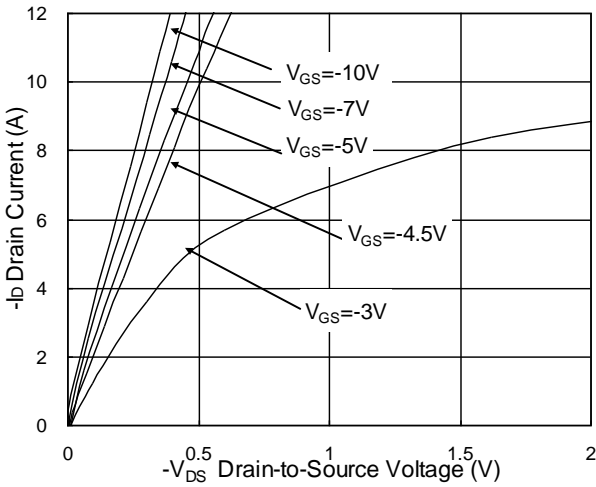


Fig.1 Typical Output Characteristics

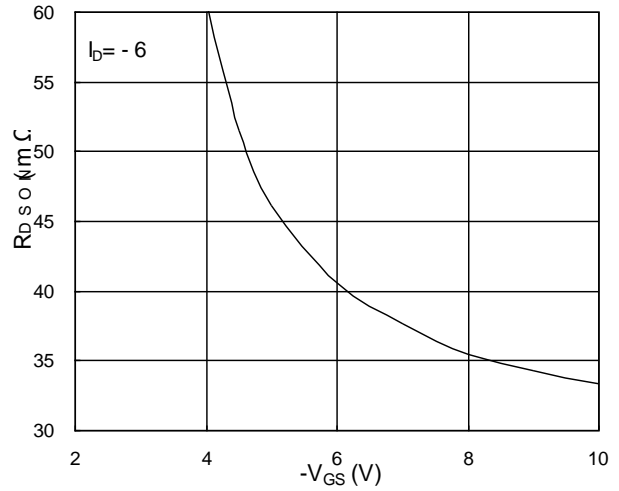


Fig.2 On-Resistance vs. G-S Voltage

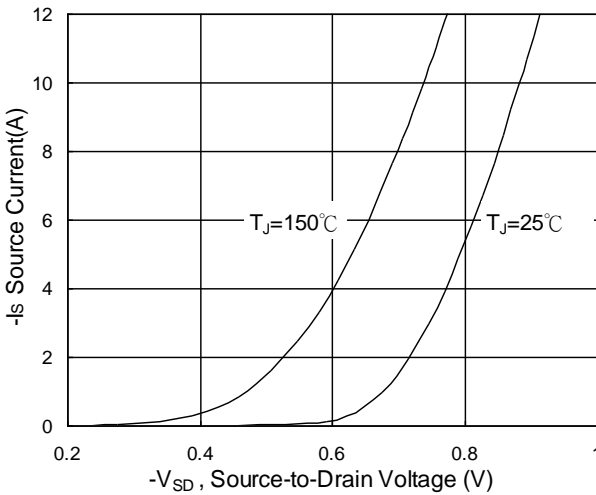


Fig.3 Source Drain Forward Characteristics

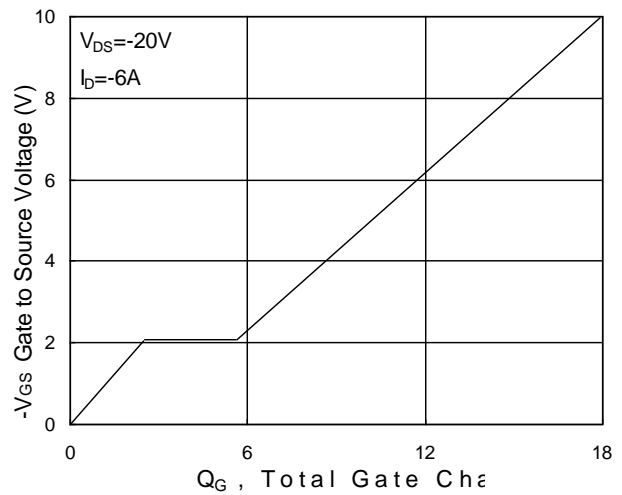


Fig.4 Gate-Charge Characteristics

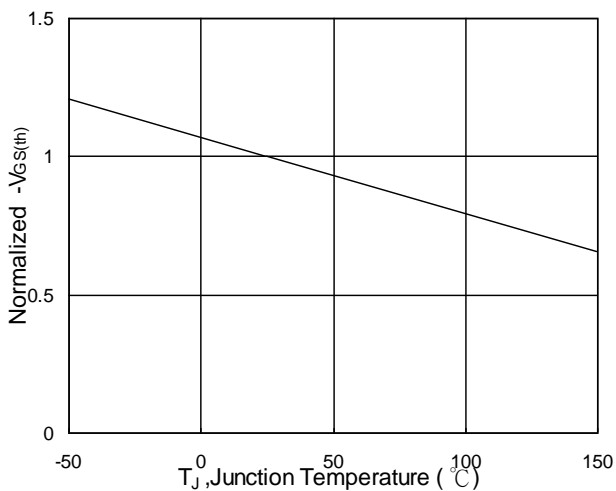


Fig.5 Normalized V_{GS(th)} vs. T_J

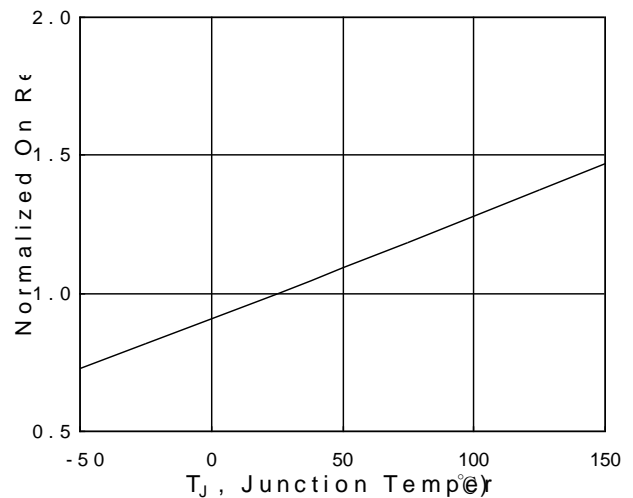


Fig.6 Normalized R_{DS(on)} vs. T_J



TM10G04S/TM4614A

N+P-Channel Enhancement Mode Mosfet

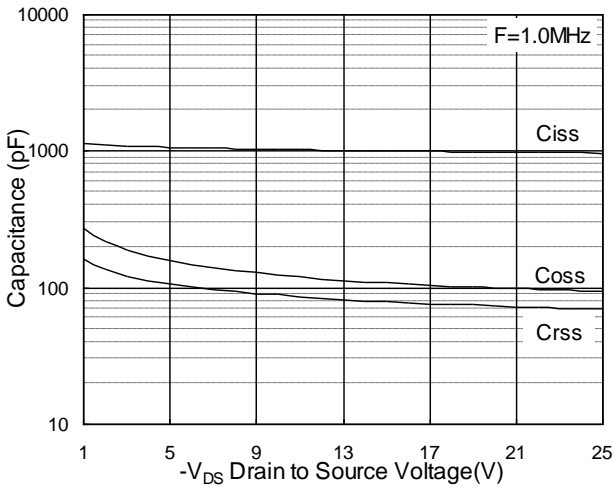


Fig.7 Capacitance

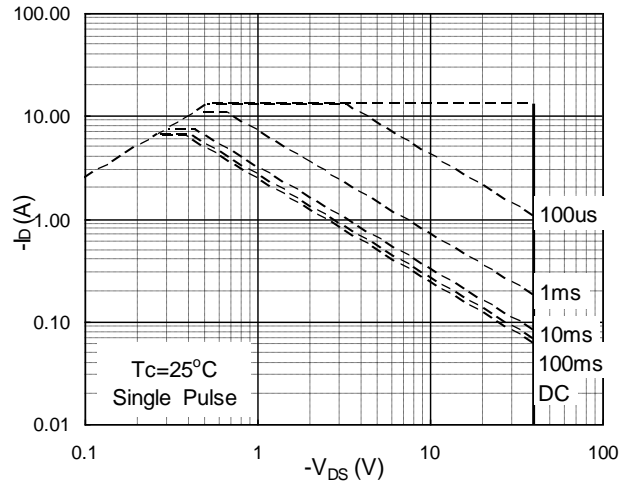


Fig.8 Safe Operating Area

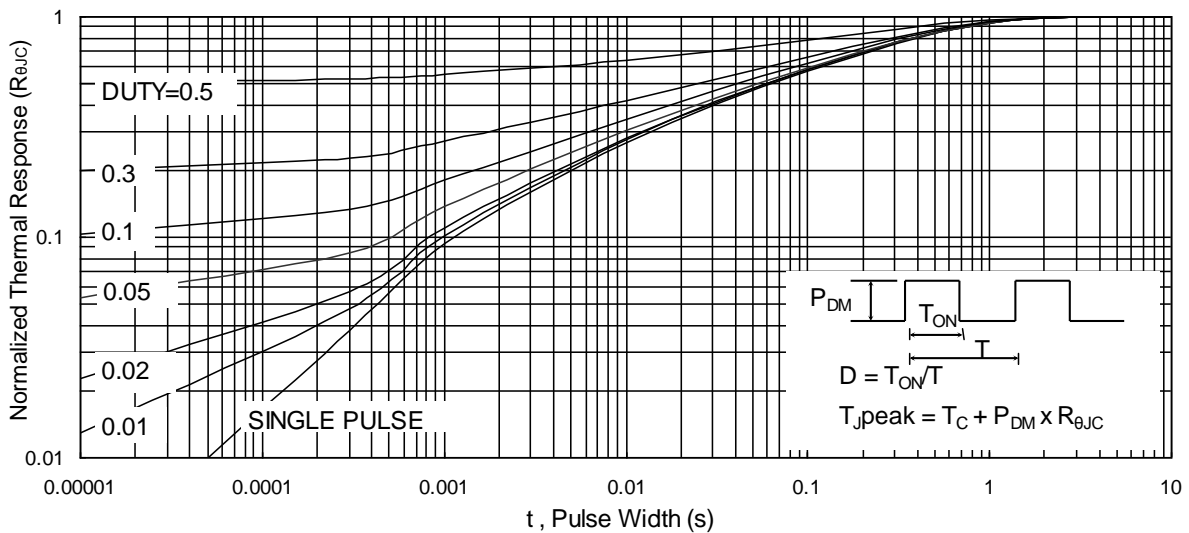


Fig.9 Normalized Maximum Transient Thermal Impedance

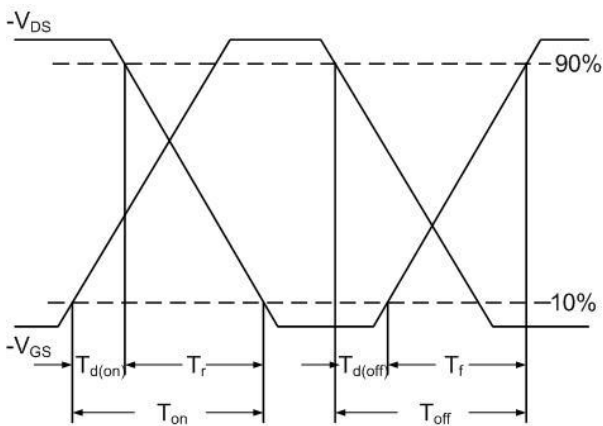


Fig.10 Switching Time Waveform

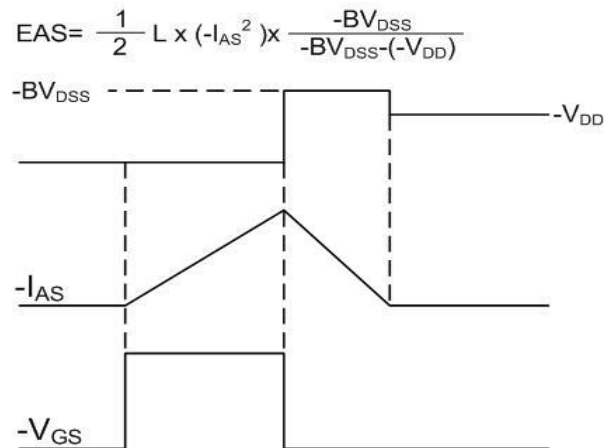
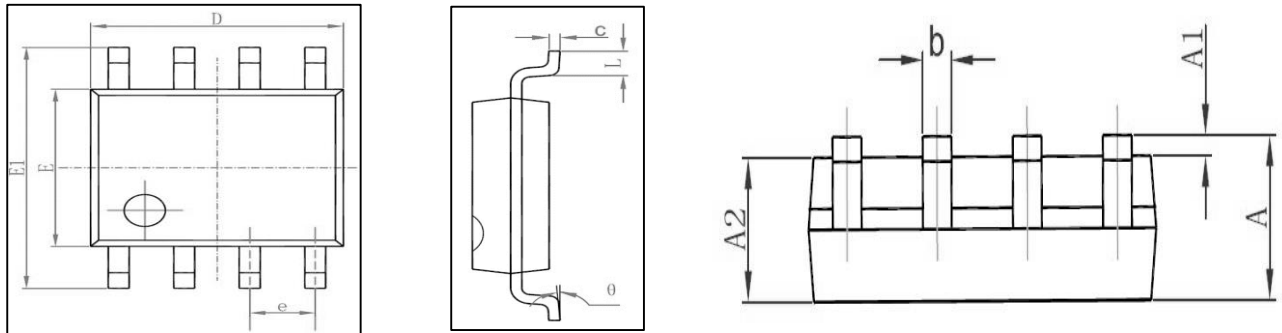
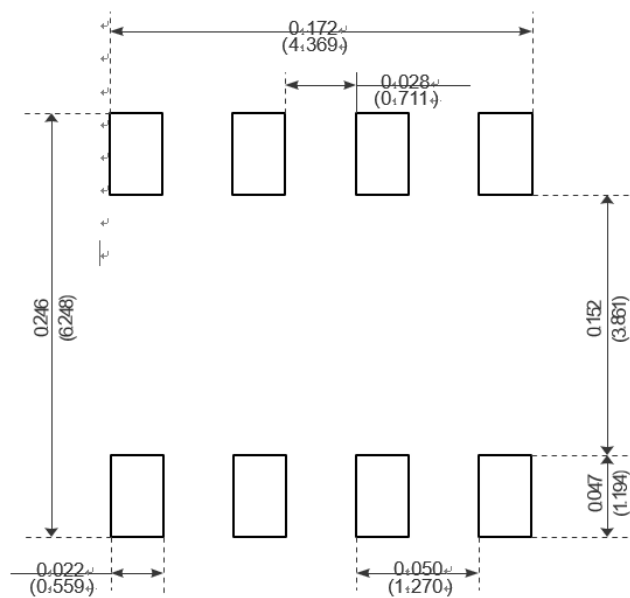


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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